

NCE Automotive N-Channel Enhancement Mode Power MOSFET

Description

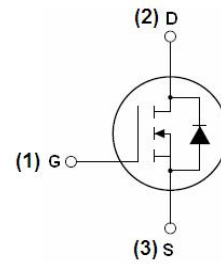
The NCEA4080K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 40V, I_D = 80A$
 - $R_{DS(ON)} < 6.6m\Omega @ V_{GS} = 10V$
 - $R_{DS(ON)} < 15.0m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- 100% UIS tested
- 100% ΔV_{ds} tested
- **AEC-Q101 qualified**

Application

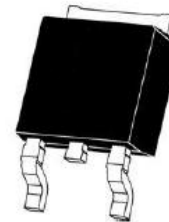
- Automotive application
- PWM
- Load Switching



Schematic diagram



Marking and pin assignment



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
A4080K	NCEA4080K	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	56.7	A
Pulsed Drain Current	I_{DM}	350	A
Maximum Power Dissipation	P_D	80	W
Derating factor		0.53	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	E_{AS}	309	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.88	$^\circ C/W$
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Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	5.3	6.6	m Ω
	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=20A$	-	8.6	15.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=20A$	-	20	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	2730	-	pF
Output Capacitance	C_{oss}		-	273	-	pF
Reverse Transfer Capacitance	C_{rss}		-	247	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, R_L=1\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	29	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	20	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	61	-	nC
Gate-Source Charge	Q_{gs}		-	10.5	-	nC
Gate-Drain Charge	Q_{gd}		-	13.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=10A$	-	-	1.2	V
Diode Forward Current	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = 20A$ $di/dt = 100A/\mu s$	-	33	-	nS
Reverse Recovery Charge	Q_{rr}		-	24	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. EAS condition : $T_J=25^\circ\text{C}, V_{DD}=20V, V_G=10V, L=0.5mH, R_G=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^\circ\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics (Curves)

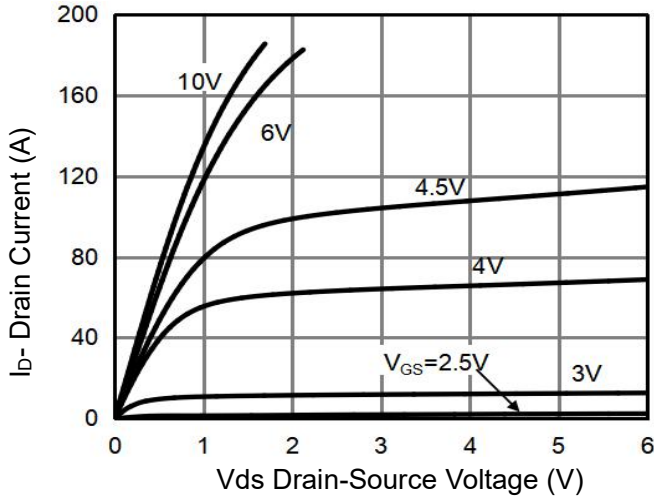


Figure 1 Output Characteristics

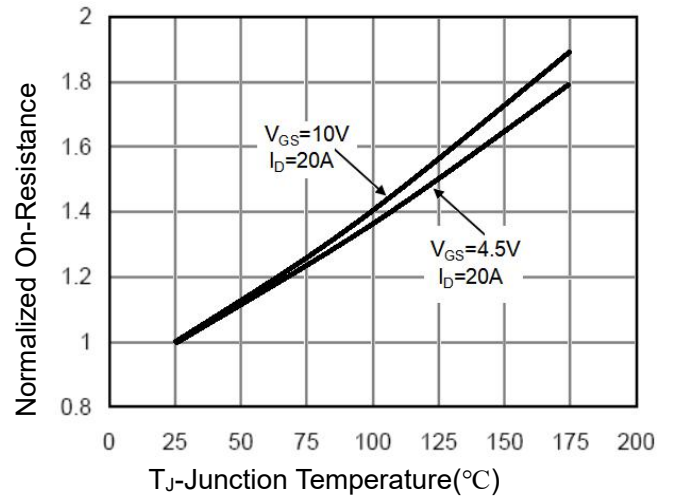


Figure 4 Rdson-Junction Temperature

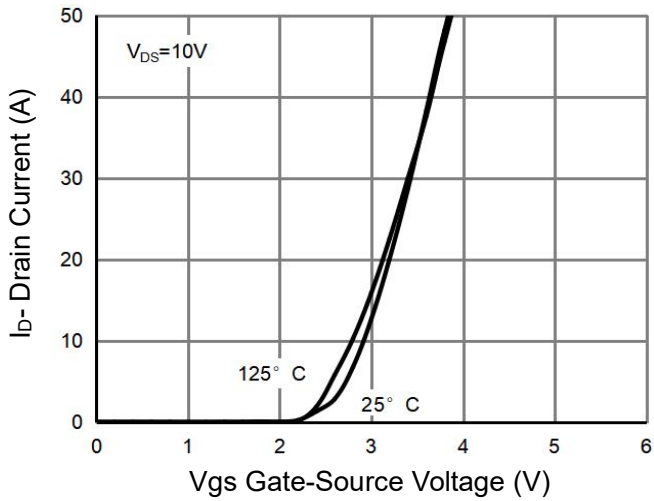


Figure 2 Transfer Characteristics

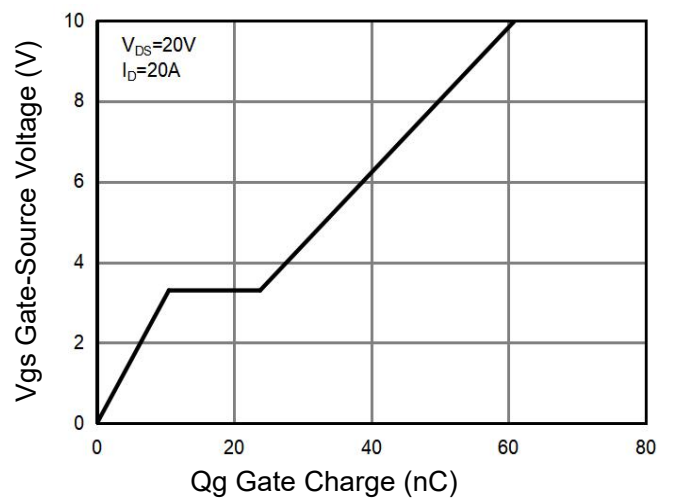


Figure 5 Gate Charge

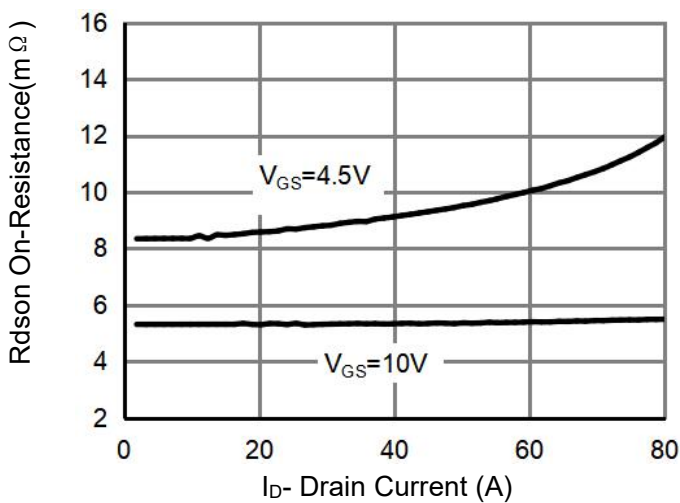


Figure 3 Rdson- Drain Current

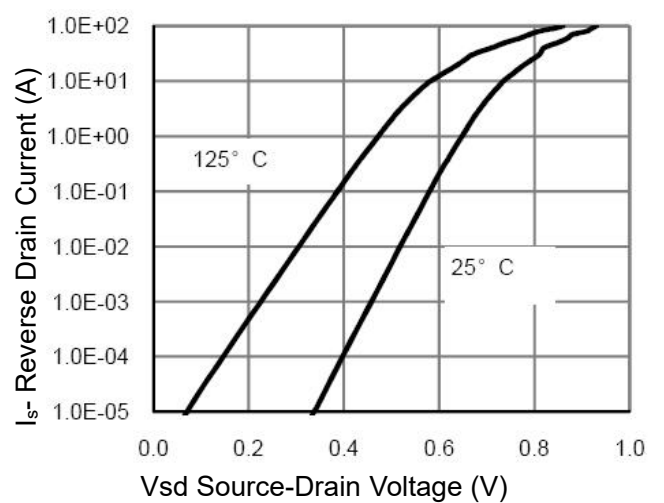


Figure 6 Source- Drain Diode Forward

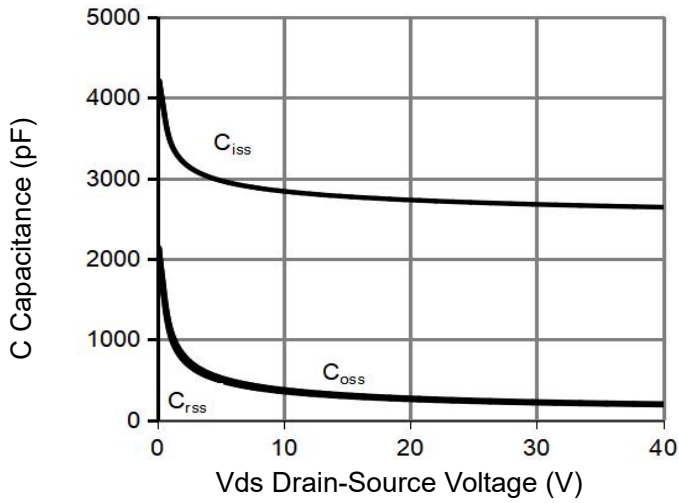


Figure 7 Capacitance vs Vds

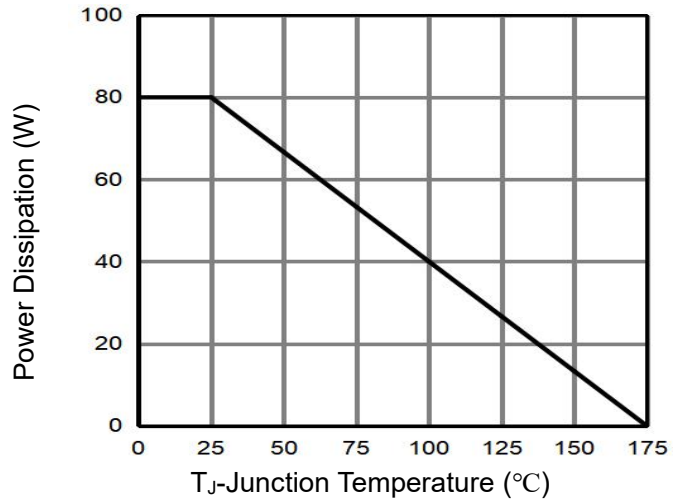


Figure 9 Power De-rating

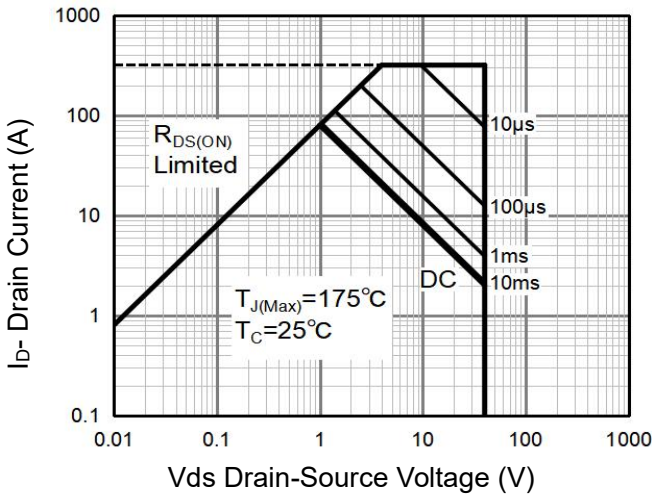


Figure 8 Safe Operation Area (Note3)

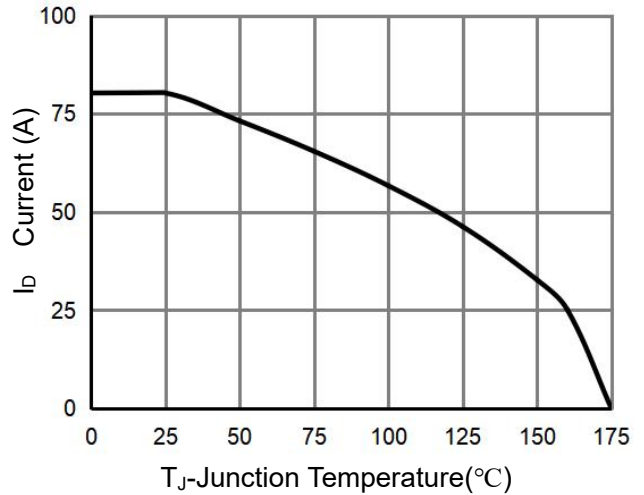


Figure 10 ID Current- Junction Temperature

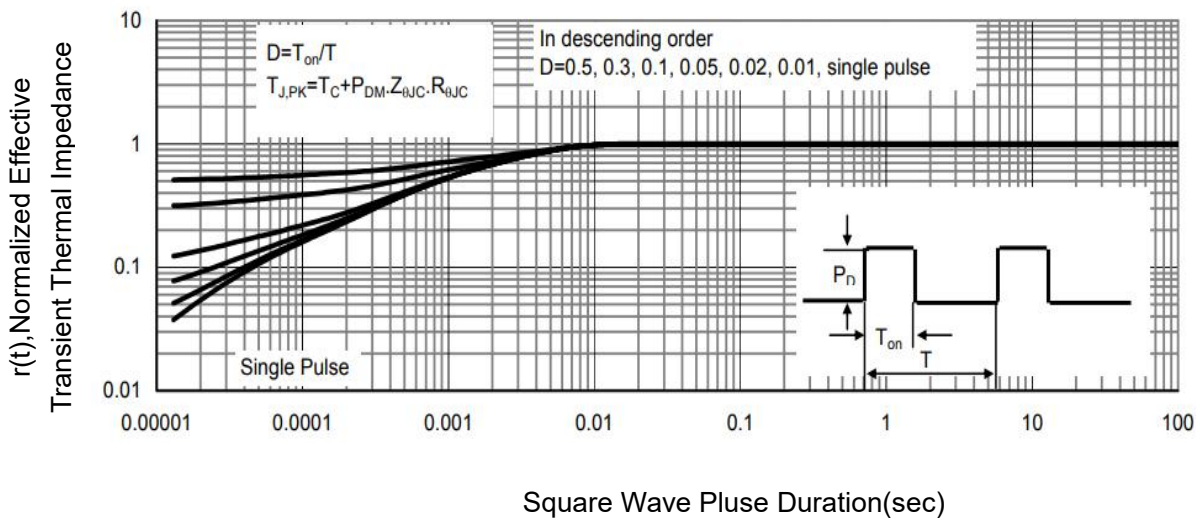
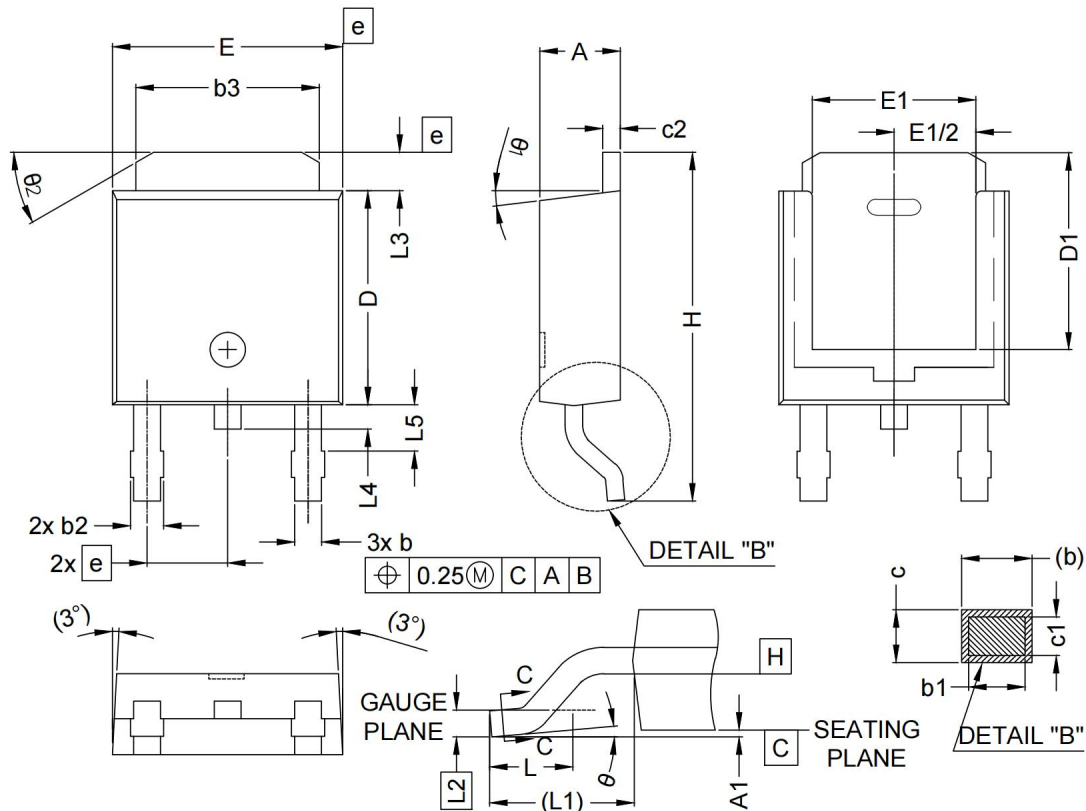


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	2.18	2.39	E	6.35	6.73	θ_1	0°	15°
A1	-	0.13	E1	4.32	-	θ_2	25°	35°
b	0.65	0.89	e	2.29 BSC				
b1	0.64	0.79	H	9.94	10.34			
b2	0.76	1.13	L	1.50	1.78			
b3	4.95	5.46	L1	2.74 REF				
c	0.46	0.61	L2	0.51 BSC				
c1	0.41	0.56	L3	0.89	1.27			
c2	0.46	0.60	L4	-	1.02			
D	5.97	6.22	L5	1.14	1.49			
D1	5.21	-	θ	0°	10°			

NOTE ; 1.0 DIMENSIONING & TOLERANCEING CONFIRM TO ASME Y14.5M-1994.
 2.0 ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.
 3.0 HEAT SINK SIDE FLASH IS MAX. 0.8mm.
 4.0 RADIUS ON TERMINAL IS OPTIONAL.

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